

SANYO	No.3769A	<h1 style="margin: 0;">2SK1468</h1> <p style="margin: 0;">N-Channel MOS Silicon FET</p> <p style="margin: 0;">Very High-Speed Switching Applications</p>
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Features

- Low ON resistance.
- Very high-speed switching.
- Low-voltage drive.

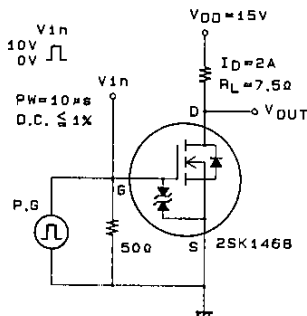
Absolute Maximum Ratings at Ta = 25°C

Drain to Source Voltage	V_{DSS}		30	V
Gate to Source Voltage	V_{GSS}		± 15	V
Drain Current(DC)	I_D		4	A
Drain Current(Pulse)	I_{DP}	$PW \leq 10\mu s, \text{ duty cycle} \leq 1\%$	16	A
Allowable Power Dissipation	P_D		1.0	W
		$T_c = 25^\circ C$	20	W
Channel Temperature	T_{ch}		150	°C
Storage Temperature	T_{stg}		- 55 to + 150	°C

Electrical Characteristics at Ta = 25°C

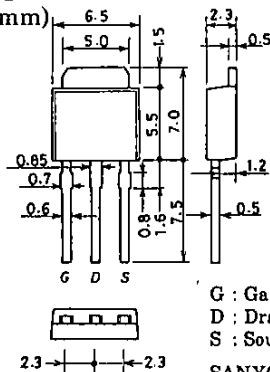
			min	typ	max	
D-S Breakdown Voltage	$V_{(BR)DSS}$	$I_D = 1mA, V_{GS} = 0$	30			V
G-S Breakdown Voltage	$V_{(BR)GSS}$	$I_G = \pm 100\mu A, V_{DS} = 0$	± 15			V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 30V, V_{GS} = 0$			100	μA
Gate to Source Leakage Current	I_{GSS}	$V_{GS} = \pm 12V, V_{DS} = 0$			± 10	μA
Cutoff Voltage	$V_{GS(off)}$	$V_{DS} = 10V, I_D = 1mA$	1.0		2.0	V
Forward Transfer Admittance	$ Y_{fs} $	$V_{DS} = 10V, I_D = 2A$	2.5	4		S
Static Drain to Source on State Resistance	$R_{DS(on)}$	$I_D = 2A, V_{GS} = 10V$	0.085	0.12		Ω
	$R_{DS(on)}$	$I_D = 2A, V_{GS} = 4V$	0.12	0.17		Ω
Input Capacitance	C_{iss}	$V_{DS} = 10V, f = 1MHz$		400		pF
Output Capacitance	C_{oss}	$V_{DS} = 10V, f = 1MHz$		250		pF
Reverse Transfer Capacitance	C_{rss}	$V_{DS} = 10V, f = 1MHz$		90		pF
Turn-ON Delay Time	$t_{d(on)}$	See specified Test Circuit.	10			ns
Rise Time	t_r	"		20		ns
Turn-OFF Delay Time	$t_{d(off)}$	"		90		ns
Fall Time	t_f	"		60		ns
Diode Forward Voltage	V_{SD}	$I_S = 4A, V_{GS} = 0$	1.0	1.5		V

Switching Time Test Circuit



Package Dimensions 2083A

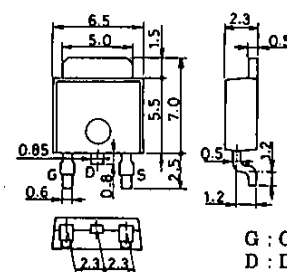
(unit : mm)



G : Gate
D : Drain
S : Source
SANYO : TP

Package Dimensions 2092A

(unit : mm)

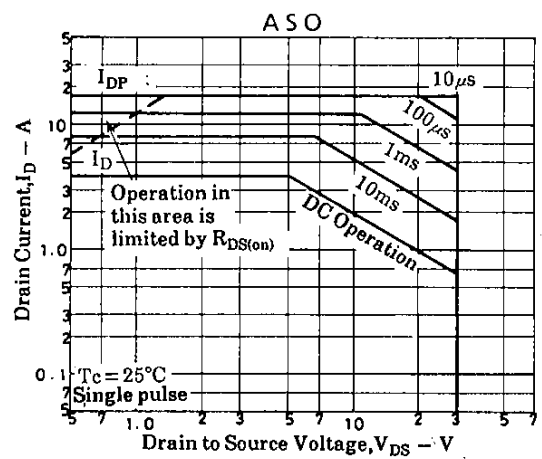
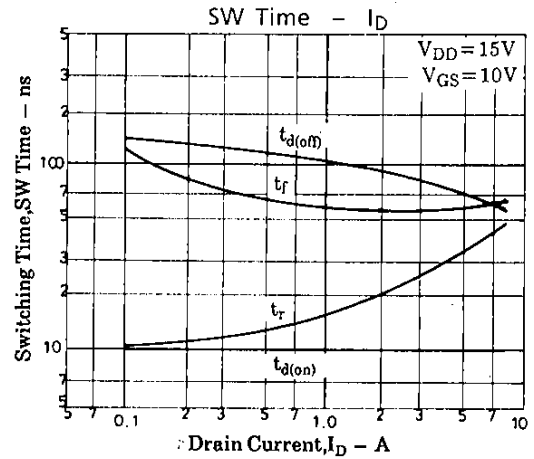
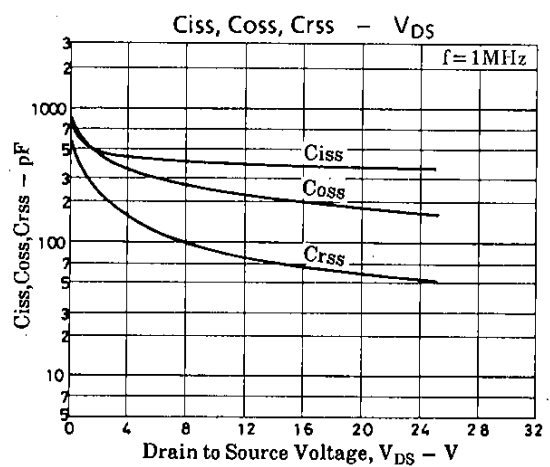
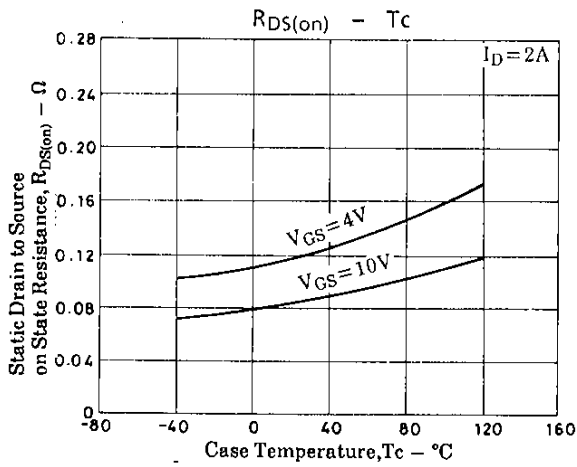
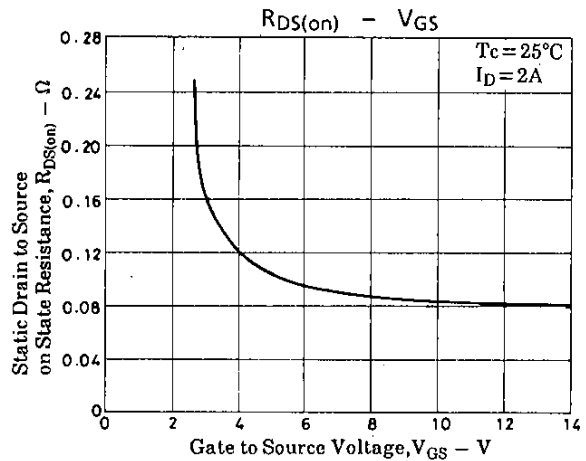
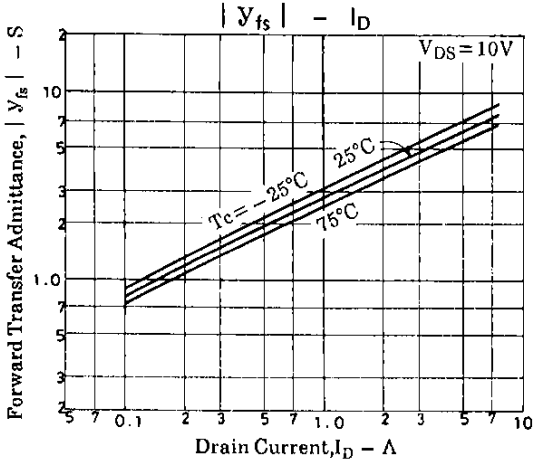
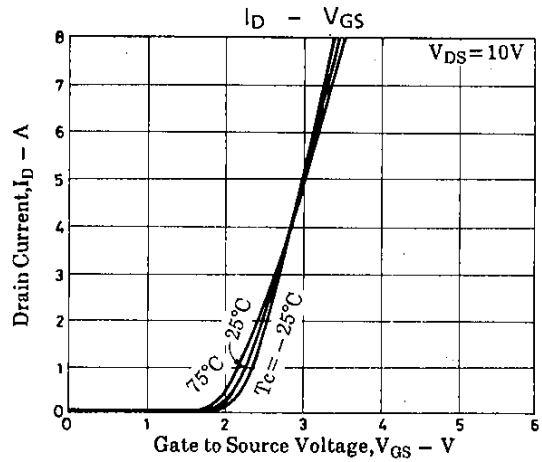
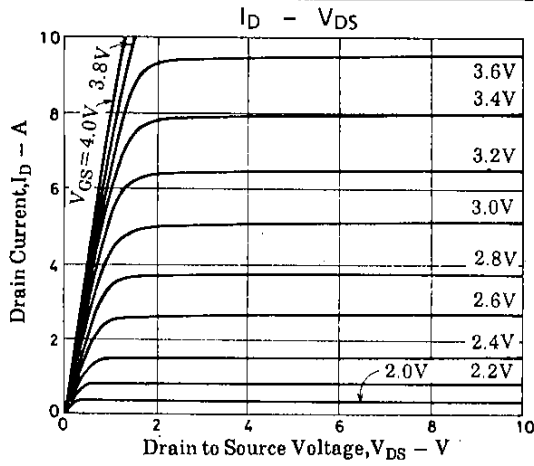


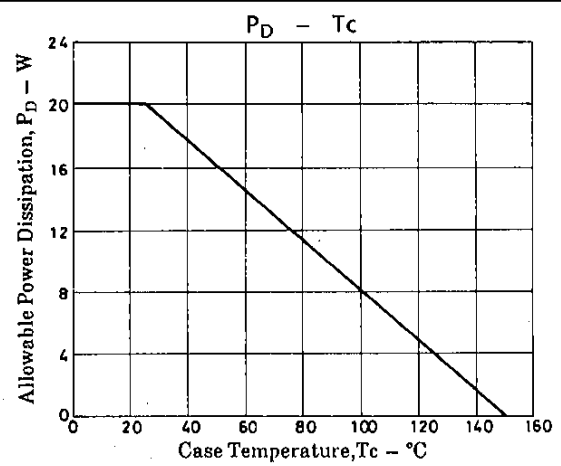
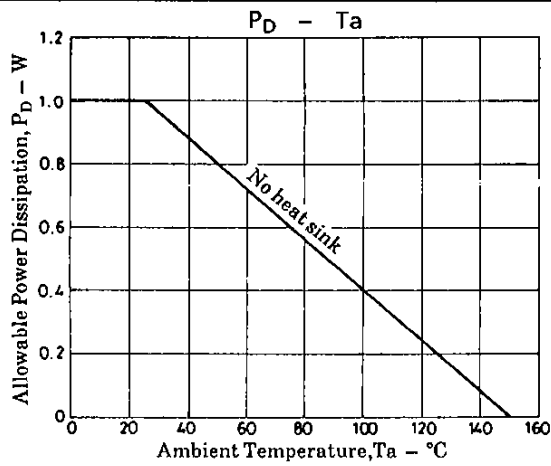
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SANYO : TP - FA

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